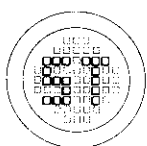


Technical Information

Index of Key Symbols

B	Base connection	K _v	Thermal resistance correction factor
C	Capacitance; junction capacitance; Collector connection	P _{tot}	Power dissipation
C _{CBO}	Collector base capacitance (open emitter)	P _D	Continuous power dissipation
C _{EBO}	Emitter base capacitance (open collector)	P _i	Pulse power dissipation
C _{iss}	Input capacitance	r _b , c _c	Collector base time constant
E	Emitter connection	r _{thA}	Pulse thermal resistance junction to ambient air
f	Frequency	r _{thC}	Pulse thermal resistance junction to case
f _r	Gain bandwidth product	R	Resistance; resistor
F	Noise figure	R _{BE}	Resistance between base and emitter
F _C	Noise figure in mixer stages	R _L	Load resistance
h	Parameters of h-(hybrid) matrix	R _S	Series resistance
h _f	Small signal current gain	R _{th}	Thermal resistance
h _i	Input impedance	R _{thA}	Thermal resistance junction to ambient air
h _o	Output admittance	R _{thC}	Thermal resistance junction to case resp. mounting base
h _r	Reverse voltage transfer ratio	R _{thC/S}	Thermal resistance case or mounting base to heat sink
h _{FE}	DC current gain, common emitter	R _{thS}	Thermal resistance heat sink to ambient air
I _B	Base current	t	Time
I _{BM}	Peak base current	t _d	Delay time
I _{B1}	Turn-on current	t _f	Fall time
I _{B2}	Turn-off current	t _{off}	Turn-off time (ts+tf)
I _C	Collector current	t _{on}	Turn-on time (td+tr)
I _{CAV}	Average collector current	t _p	Pulse duration
I _{CBO}	Collector base cutoff current (open emitter)	t _{pd}	Propagation delay time
I _{CEO}	Collector emitter cutoff current (open base)	t _r	Rise time
I _{CER}	Collector emitter cutoff current (specified resistance between base and emitter)	t _s	Storage time
I _{CES}	Collector emitter cutoff current (base short-circuited to emitter)	t _{total}	Total switching time (ton+toff)
I _{CEV}	Collector emitter cutoff current (specified voltage between base and emitter)	T	Temperature; duration of one period
I _{CM}	Peak collector current	T _{amb}	Ambient temperature
I _E	Emitter current	T _J	Junction temperature
I _{EBO}	Emitter base cutoff current (open collector)	T _C	Case temperature
		T _S	Storage temperature
		T _{SB}	Temperature of substrate backside



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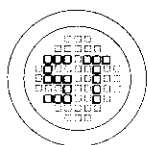
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Technical Information

Index of Key Symbols

V	Voltage
V_{BB}	Base supply voltage
V_{BE}	Base emitter voltage
V_{BEsat}	Base emitter saturation voltage
$V_{(BR)CBO}$	Collect base breakdown voltage (open emitter)
$V_{(BR)CEO}$	Collector emitter breakdown voltage (open base)
$V_{(BR)CER}$	Collector emitter breakdown voltage (specified resistance between base and emitter)
$V_{(BR)CES}$	Collector emitter breakdown voltage (emitter short-circuited to base)
$V_{(BR)EBO}$	Emitter base breakdwon voltage (open collector)
V_{CB}	Collector base voltage
V_{CBO}	Collector base voltage (open emitter)
V_{CC}	Collector supply voltage
V_{CE}	Collector emitter voltage
V_{CEO}	Collector emitter voltage (open base)
V_{CER}	Collector emitter voltage (specified resistance between base and emitter)
V_{CES}	Collector emitter voltage (emitter short-circuit to base)
V_{CEsat}	Collector emitter saturation voltage
V_{CEV}	Collector emitter voltage (specified voltage between base and emitter)
V_{EBO}	Emitter base voltage (open collector)
V_{EE}	Emitter supply voltage
V_i	Input voltage
V_o	Output voltage
T_s	Storage time constant
V	Duty cycle (tp/T)



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